

[First Hit](#) [Previous Doc](#) [Next Doc](#) [Go to Doc#](#)

End of Result Set



Generate Collection

Print

L6: Entry 1 of 1

File: EPAB

Mar 24, 1994

PUB-NO: DE004331519A1

DOCUMENT-IDENTIFIER: DE 4331519 A1

TITLE: Fine pattern prodn with high resolution using simplified efficient method -
by applying first photoresist, silylating and glassifying surface, making mask with
second resist layer and etching down to

PUBN-DATE: March 24, 1994

INVENTOR-INFORMATION:

NAME

COUNTRY

HAN, WOO-SUNG

KR

ASSIGNEE-INFORMATION:

NAME

COUNTRY

SAMSUNG ELECTRONICS CO LTD

KR

APPL-NO: DE04331519

APPL-DATE: September 16, 1993

PRIORITY-DATA: KR09216931A (September 17, 1992)

US-CL-CURRENT: 430/312

INT-CL (IPC): G03F 7/11; G03F 7/20; G03F 7/40

EUR-CL (EPC): G03F007/09

ABSTRACT:

Prodn. of a fine pattern comprises the stages: (1) coating a process substrate (I) with photoresist (II) to form a first resist layer (III) and silylation of the surface to form a silylated layer (IV); (2) glassifying (V) with O₂ to form a glassified layer (V); (3) coating (V) with (II) to form a second resist layer (VI); (4) selective exposure and development of (VI) in a given pattern; and (5) etching (V) and (III), using (VI) as mask. ADVANTAGE - Prodn. of a fine pattern is simplified and the productivity is increased, since (V) is used as intermediate layer. The resolution is high. In an example, a Si wafer (1) was coated with chemically amplified resist (2). This was silylated in gas or aq. phase to form a 2000-3000 Å thick silylation layer (21) and glassified with O₂ (22) in RIE appts., forming a glassified layer (23) of SiO_x in the organic material. A second resist layer (4) was applied, exposed with UV light (5) through a photomask (6) and developed. The glassified layer was etched with 100 Ncc O₂/min at an energy of 2 kW, then the first resist was etched in 25Ncc CF₄/min + 60 Ncc O₂/min at 2kW in the same appts.

[Previous Doc](#)[Next Doc](#)[Go to Doc#](#)